

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Before line 1 of page 1 of the Specification please insert:

--This nonprovisional application claims priority under 35 U.S.C. § 119(a) on Patent Application No. 2002-353937 filed in JAPAN on December 5, 2002, which is herein incorporated by reference.--

Please replace paragraph [0011] as follows:

[0011] A method of measuring electrical capacitance in accordance with ~~one or more embodiments~~ an embodiment of the present invention is such that ~~one or more~~ a scanning capacitance microscopes is provided for detecting ~~one or more surfaces~~ at least one surface by means of ~~one or more~~ at least one electrically conductive probes are used to measure ~~one or more~~ electrical capacitances of ~~one or more~~ semiconductor surfaces<sub>7</sub>. ~~the~~ The method comprising ~~one or more~~ a first steps wherein ~~one or more~~ at least one clean surfaces are is formed on ~~one or more~~ at least one semiconductor samples by surface treatment<sub>7</sub>. ~~one or more second steps wherein at least one of the semiconductor sample or samples~~ In a second step, the at least one semiconductor sample on which ~~one or more~~ at least one clean surfaces were was formed ~~at at least one of the first step or steps~~ is promptly (preferably within 10 minutes) placed in ~~one or more~~ an ultrahigh vacuum environments (e.g., an ultrahigh vacuum environment of on the order of  $1.33 \times 10^{-7}$  Pa ( $1 \times 10^{-9}$  Torr)) ~~or one or more~~ or in an inert gas.

~~environments and is maintained therein, and one or more third steps wherein one or more~~ In a third step, at least one electrically conductive probes, on ~~one or more~~ a surfaces of which ~~one or more~~ an insulating films ~~are~~ is formed, are ~~is~~ used to measure ~~one or more~~ the electrical capacitances of ~~the~~ at least one of the semiconductor sample surface ~~or surfaces~~ maintained in one ~~or more~~ the ultrahigh vacuum environments or ~~one or more~~ in the inert gas environments at at least one of the second step or steps.

Please add new paragraph [0011A] as follows:

[0011A] In another embodiment, the method of measuring an electrical capacitance is such that a plurality of scanning capacitance microscopes are provided for detecting a plurality of surfaces by means of each microscope having an electrically conductive probe used to measure electrical capacitances of semiconductor surfaces. The method comprising a plurality of first steps, i.e., a first step for each individual microscope, wherein at least one clean surface is formed on semiconductor samples by surface treatment. In a plurality of second steps, the semiconductor samples on which at least one clean surface was formed are promptly (preferably within 10 minutes) placed in at least one ultrahigh vacuum environment (e.g., an ultrahigh vacuum environment of on the order of  $1.33 \times 10^{-7}$  Pa ( $1 \times 10^{-9}$  Torr)) or in at least one inert gas environment and are maintained therein. In a plurality of third steps, a plurality of electrically conductive probes, i.e., one for each microscope, on each surface of which an insulating film is formed, are used to measure the electrical capacitances of the at least one of the semiconductor sample

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surface maintained in the at least one ultrahigh vacuum environment  
or in the at least one inert gas environment.